



A Product Line of Diodes Incorporated

ZXTD2090DE6

#### **50V DUAL NPN LOW SATURATION SWITCHING TRANSISTOR IN SOT26**

#### Features

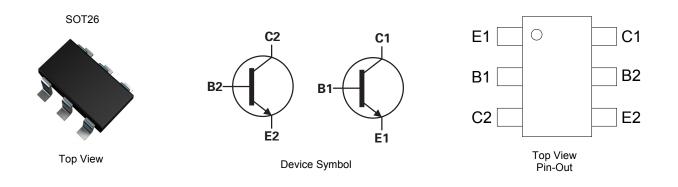
- BV<sub>CEO</sub> > 50V
- I<sub>C</sub> = 1A High Continuous Current
- High Gain
- R<sub>SAT</sub> = 160mΩ for Low Equivalent On Resistance
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -270mV @ 1A</li>
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (approximate)

## Applications

- LCD Backlighting Inverter Circuits
- Boost Functions in DC-DC Converters



## Ordering Information (Notes 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTD2090DE6TA	2090	7	8	3,000

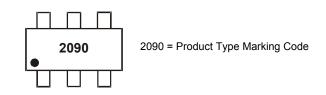
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**





## Maximum Ratings – Q1 & Q2 Common (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	lc	1	А
Peak Pulse Current	I <sub>CM</sub>	2	А
Base current	IB	200	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 9)		0.7 5.6		
	(Notes 6 & 9)		0.9 7.2	W mW/°C	
Power Dissipation Linear Derating Factor	(Notes 6 & 10)	PD	1.1 8.8		
	(Notes 7 & 9)		1.1 8.8		
	(Notes 8 & 9)		1.7 13.6		
	(Notes 5 & 9)		179	°C/W	
	(Notes 6 & 9)		139		
Thermal Resistance, Junction to Ambient	(Notes 6 & 10)	$R_{ heta}$ JA	113		
	(Notes 7 & 9)		113		
	(Notes 8 & 9)		73		
Thermal Resistance, Junction to Lead	(Note 11)	$R_{ extsf{ heta}JL}$	95.50		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	Ο°		

Notes: 5. For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as note (6), except the device is surface mounted on 25mm x 25mm 1oz copper.

7. Same as note (6), except the device is surface mounted on 50mm x 50mm 2oz copper.

8. Same as note (8), except the device is measured at t < 5 seconds.

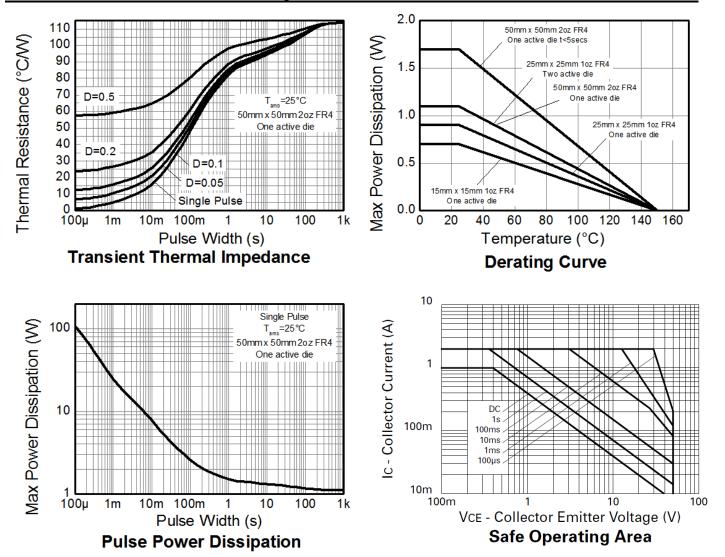
9. For device with one active die, both collectors attached to a common heatsink.

10. For device with two active dice running at equal power, split heatsink 50% to each collector.

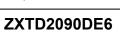
11. Thermal resistance from junction to solder-point (at the end of the collector lead).



### **Thermal Characteristics and Derating Information**



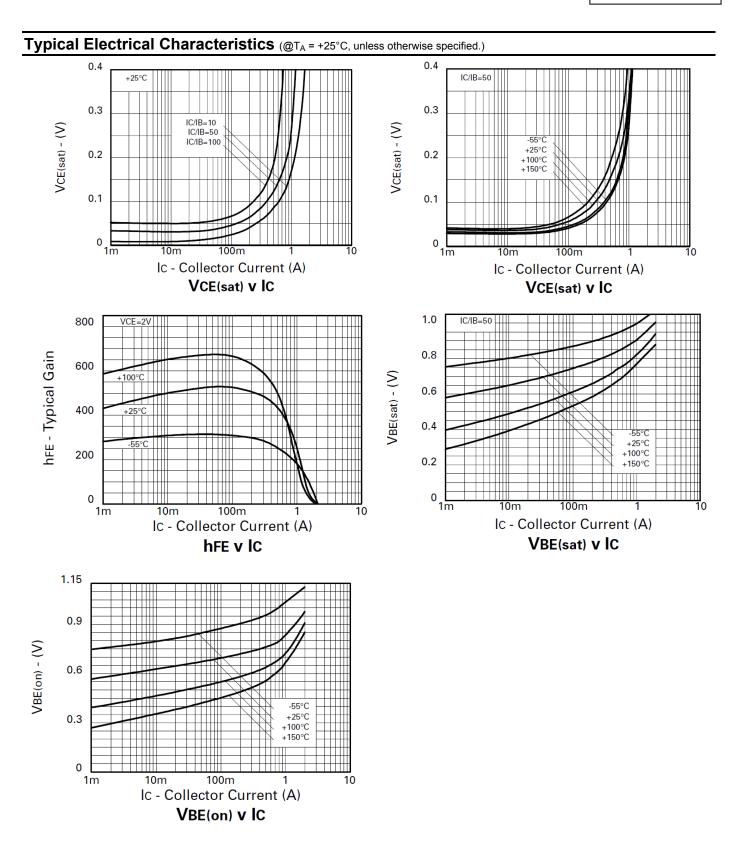




Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50			V	I <sub>C</sub> = 100μΑ
Collector-Emitter Breakdown Voltage (Note 12)	BV <sub>CEO</sub>	50			V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7			V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current	ICBO			10	nA	V <sub>CB</sub> = 40V
Collector-Emitter Cutoff Current	ICES			10	nA	V <sub>CES</sub> = 40V
Emitter Cutoff Current	I <sub>EBO</sub>			10	nA	V <sub>EB</sub> = 5.6V
DC Current Gain (Note 12)	h <sub>FE</sub>	200 300 200 75 20	420 450 350 130 60			$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 100 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 500 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 1.5 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 12)	V <sub>CE(sat)</sub>		24 60 120 160	35 80 200 270	mV	$\begin{split} I_{C} &= 100 \text{mA}, \ I_{B} &= 10 \text{mA} \\ I_{C} &= 250 \text{mA}, \ I_{B} &= 10 \text{mA} \\ I_{C} &= 500 \text{mA}, \ I_{B} &= 10 \text{mA} \\ I_{C} &= 1A, \ I_{B} &= 50 \text{mA} \end{split}$
Base-Emitter Saturation Voltage (Note 12)	V <sub>BE(sat)</sub>		940	1100	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA
Base-Emitter Turn-On Voltage (Note 12)	V <sub>BE(on)</sub>		850	1100	mV	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
Output Capacitance	C <sub>obo</sub>		10		pF	V <sub>CB</sub> = 10V. f = 1MHz
Current Gain-Bandwidth Product	fT		215		MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA f = 100MHz
Turn-On Time	t <sub>on</sub>		150		ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A
Turn-Off Time	t <sub>off</sub>		425		ns	I <sub>B1</sub> = I <sub>B2</sub> = 100mA

Note: 12. Measured under pulsed conditions. Pulse width  $\leq$  300 µs. Duty cycle  $\leq$  2%

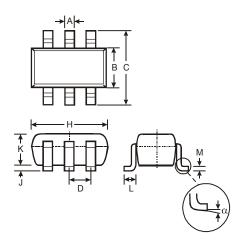






# **Package Outline Dimensions**

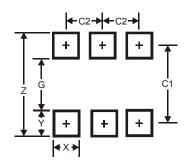
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D		_	0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
Κ	1.00	1.30	1.10		
L	0.35	0.55	0.40		
Μ	0.10	0.20	0.15		
α	0°	8°	_		
All D	All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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